

MA2SD10

Silicon epitaxial planar type

For super-high speed switching circuit

■ Features

- Sealed in the super small SS-mini type 2-pin package
- Allowing to rectify under ($I_{F(AV)} = 200$ mA) condition
- Low forward rise voltage V_F
- Allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

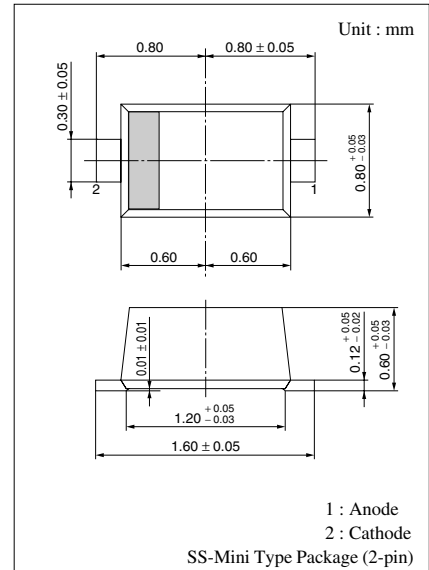
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	20	V
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 10$ V			20	μA
Forward voltage (DC)	V_{F1}	$I_F = 5$ mA			0.27	V
	V_{F2}	$I_F = 200$ mA			0.47	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		40		pF

- Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.
2. Rated input/output frequency: 250 MHz



Marking Symbol: 2L

Internal Connection

